ACS240MS

Radiation Hardened Inverting, Octal, Three-State Buffer/Line Driver

March 1998

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25Micron Radiation Hardened SOS CMOS
- · Radiation Environment
 - Latch-up Free Under any Conditions
- SEU LET Threshold>100MeV/(mg/cm²)
- Input Logic Levels $V_{IL} = (0.3V)(V_{CC})$, $V_{IH} = (0.7V)(V_{CC})$
- Quiescent Supply Current......20μA

Applications

- · Databus Driving
- Data Routing
- Redundant Data Control Circuitry

Description

The Radiation Hardened ACS240MS is an Inverting, Octal, Three-State Buffer/Line Driver with two active-LOW Enable inputs (\overline{AE} and \overline{BE}). Each Enable input controls four outputs. When an Enable input is LOW, the corresponding outputs are active and input signals are inverted. A HIGH on an Enable input causes the corresponding outputs to be high impedance, regardless of the input levels.

The ACS240MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

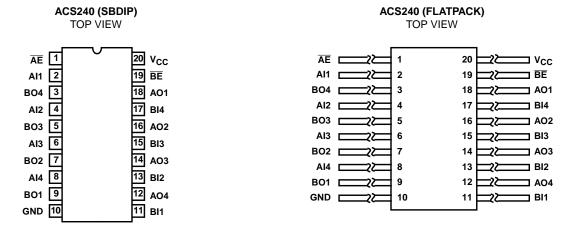
Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACS240 are contained in SMD 5962-98540. A "hot-link" is provided on our homepage with instructions for downloading. http://www.intersil.com/data/sm/index.htm

Ordering Information

SMD PART NUMBER	INTERSIL PART NUMBER	TEMP. RANGE (°C)	PACKAGE	CASE OUTLINE
5962F9854001VRC	ACS240DMSR-02	-55 to 125	20 Ld SBDIP	CDIP2-T20
N/A	ACS240D/Sample-02	25	20 Ld SBDIP	CDIP2-T20
5962F9854001VXC	ACS240KMSR-02	-55 to 125	20 Ld Flatpack	CDFP4-F20
N/A	ACS240K/Sample-02	25	20 Ld Flatpack	CDFP4-F20
N/A	ACS240HMSR-02	25	Die	N/A

Pinouts



ACS240MS

Die Characteristics

DIE DIMENSIONS:

Size: $2540\mu m \times 2540\mu m$ (100 mils x 100mils) Thickness: $525\mu m \pm 25\mu m$ (20.6 mils ± 1 mil) Bond Pad: $110\mu m \times 110\mu m$ (4.3 x 4.3 mils)

METALLIZATION: Al

Metal 1 Thickness: $0.7\mu m \pm 0.1\mu m$ Metal 2 Thickness: $1.0\mu m \pm 0.1\mu m$

SUBSTRATE POTENTIAL:

Unbiased Insulator

PASSIVATION

Type: Phosphorous Silicon Glass (PSG)

Thickness: $1.30\mu m \pm 0.15\mu m$

SPECIAL INSTRUCTIONS:

Bond V_{CC} First

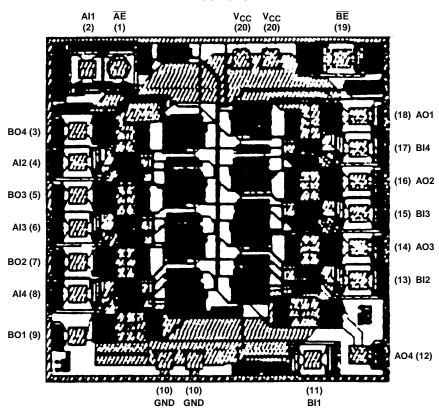
ADDITIONAL INFORMATION:

Worst Case Density: <2.0 x 10⁵ A/cm²

Transistor Count: 198

Metallization Mask Layout

ACS240MS



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